


### IN THE CLAIMS

Please cancel claims 7-17 without prejudice.



1. (Amended)      A semiconductor device, comprising

a trench formed in a substrate;

a diffusion region surrounding the trench to form a buried plate;

a first conductive material formed in the trench connecting to the buried plate through a bottom portion and a lower portion of the sidewalls of the trench to form a first electrode;

a second conductive material disposed in the trench to form a second electrode; and

a node dielectric layer formed between the first electrode and the second electrode.

### REMARKS

Claims 1-17 are pending in the application. Claims 7-17 have been canceled without prejudice in response to the finality of the restriction requirement. Claims 1-6 are rejected. By the present amendment, claim 1 has been amended. The Examiner's reconsideration of the claim rejections in view of the following amendments and remarks is respectfully requested.

#### Claim Rejections- 35 U.S.C. § 102

By the Office Action, claims 1,2,3,4, and 6 are rejected under 35 U.S.C. 102(b) as being anticipated by Park (US 5,677,225) for the reasons set forth on pages 2-3 of the Office Action.

Claim 1 of the present invention as amended includes, *inter alia*, "...a first conductive material formed in the trench connecting to the buried plate through a bottom portion and a lower